

In the Claims

Claims 1-18 (canceled).

Claim 19 (currently amended): A capacitor construction comprising:

 a first capacitor electrode comprising having a planar surface of conductively-doped silicon;

 a second capacitor electrode over the first capacitor electrode and comprising one or more materials selected from the group consisting of metals and metal compounds;

 a first dielectric layer between the first and second capacitor electrodes, the first dielectric layer comprising aluminum oxide;

 a second dielectric layer between the first and second capacitor electrodes, the second dielectric layer comprising a metal oxide other than aluminum oxide;

 wherein the first dielectric layer is between the second dielectric layer and the conductively-doped silicon; and

 wherein the metal oxide of the second dielectric layer is in physical contact with the second capacitor electrode.

Claim 20 (original): The capacitor construction of claim 19 further comprising one or more additional dielectric layers between the first and second capacitor electrodes besides the first and second dielectric layers.

Claim 21 (original): The capacitor construction of claim 19 wherein the first and second dielectric layers are the only dielectric layers between the first and second capacitor electrodes.

Claim 22 (original): The capacitor construction of claim 21 wherein the first and second dielectric layers have a combined thickness of from about 25Å to about 150Å.

Claim 23 (original): The capacitor construction of claim 22 wherein the first dielectric layer has a thickness of from about 5Å to about 60Å.

Claim 24 (original): The capacitor construction of claim 22 wherein the second dielectric layer has a thickness of from about 20Å to about 90Å.

Claim 25 (original): The capacitor construction of claim 21 wherein the first and second dielectric layers have a combined thickness of from about 25Å to about 80Å.

Claim 26 (original): The capacitor construction of claim 25 wherein the first dielectric layer has a thickness of from about 5Å to about 20Å.

Claim 27 (original): The capacitor construction of claim 25 wherein the second dielectric layer has a thickness of from about 20Å to about 60Å.

Claim 28 (original): The capacitor construction of claim 19 wherein the metal oxide of the second dielectric layer is selected from the group consisting of hafnium oxide, tantalum oxide and zirconium oxide.

Claim 29 (original): The capacitor construction of claim 28 wherein the second dielectric layer consists essentially of hafnium oxide.

Claim 30 (original): The capacitor construction of claim 28 wherein the second dielectric layer consists of hafnium oxide.

Claim 31 (original): The capacitor construction of claim 28 wherein the second dielectric layer consists essentially of tantalum oxide.

Claim 32 (original): The capacitor construction of claim 28 wherein the second dielectric layer consists of tantalum oxide.

Claim 33 (original): The capacitor construction of claim 28 wherein the second dielectric layer consists essentially of zirconium oxide.

Claim 34 (original): The capacitor construction of claim 28 wherein the second dielectric layer consists of zirconium oxide.

Claim 35 (original): The capacitor construction of claim 19 wherein the aluminum oxide of the first dielectric layer is physically against the conductively-doped silicon of the first capacitor electrode.

Claim 36 (currently amended): The capacitor construction of claim 19 wherein:

- the first dielectric layer consists of aluminum oxide;
- the first dielectric layer has a pair of opposing surfaces;
- one of the opposing surfaces of the first dielectric layer is physically against the conductively-doped silicon surface of the first capacitor electrode; and
- the other of the opposing surfaces of the first dielectric layer is physically against the metal oxide of the second dielectric layer.

Claim 37 (original): The capacitor construction of claim 36 wherein the first dielectric layer has a thickness between the opposing surfaces of from about 5Å to about 20Å.

Claim 38 (original): The capacitor construction of claim 36 wherein the second dielectric layer consists of hafnium oxide.

Claim 39 (original): The capacitor construction of claim 36 wherein the second dielectric layer consists of tantalum oxide.

Claim 40 (original): The capacitor construction of claim 36 wherein the second dielectric layer consists of zirconium oxide.

Claim 41 (currently amended): A DRAM array comprising:

a plurality of wordlines;

a plurality of bitlines; and

a plurality of capacitor constructions electrically accessible through the wordlines and bitlines, at least one of the capacitor constructions including:

a first capacitor electrode comprising a planar surface of
conductively-doped silicon;

a second capacitor electrode over the first electrode and
comprising one or more materials selected from the group consisting
of metals and metal compounds;

a first dielectric layer between the first and second
capacitor electrodes, the first dielectric layer comprising aluminum
oxide;

a second dielectric layer between the first and second
capacitor electrodes, the second dielectric layer comprising a metal
oxide other than aluminum oxide;

wherein the first dielectric layer is between the second
dielectric layer and the conductively-doped silicon; and

wherein the metal oxide of the second dielectric layer is
in physical contact with the second capacitor electrode.

Claim 42 (currently amended): An electronic system comprising:

 a memory device; and

 a processor in electrical communication with the memory device; and

 wherein at least one of the memory device and the processor includes a memory cell comprising a capacitor construction which includes:

 a first capacitor electrode comprising a planar surface of conductively-doped silicon;

 a second capacitor electrode over the first electrode and comprising one or more materials selected from the group consisting of metals and metal compounds;

 a first dielectric layer between the first and second capacitor electrodes, the first dielectric layer comprising aluminum oxide;

 a second dielectric layer between the first and second capacitor electrodes, the second dielectric layer comprising a metal oxide other than aluminum oxide;

 wherein the first dielectric layer is between the second dielectric layer and the conductively-doped silicon; and

 wherein the metal oxide of the second dielectric layer is in physical contact with the second capacitor electrode.

Claims 43-62 (canceled).